

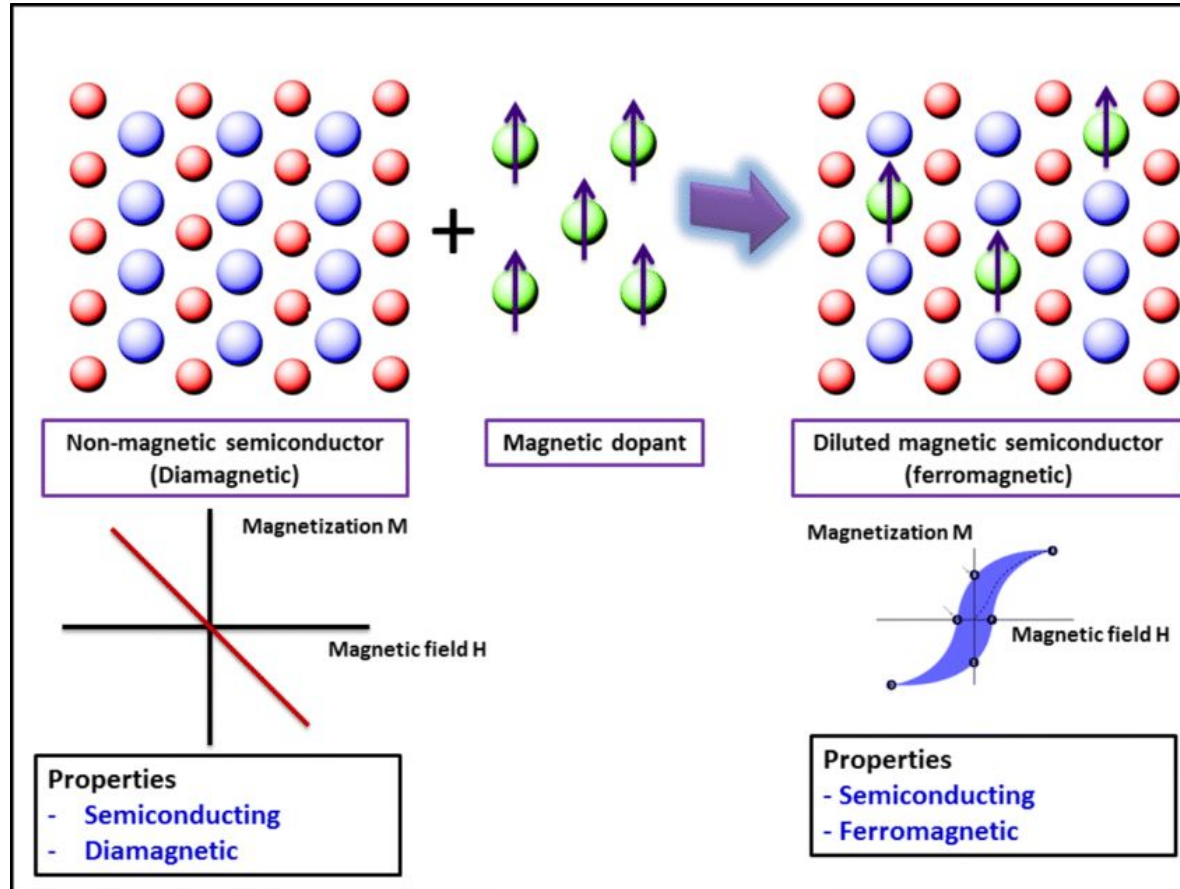
Mn-doped monolayer MoS₂: An atomically thin dilute magnetic semiconductor

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References:

- A. Ramasubramaniam and D. Naveh, Phys. Rev. B, 2013, 87, 195201
- Caleb's Paper: Quantum Imaging of Single-Atom Spin-Splitting in a Monolayer Semiconductor

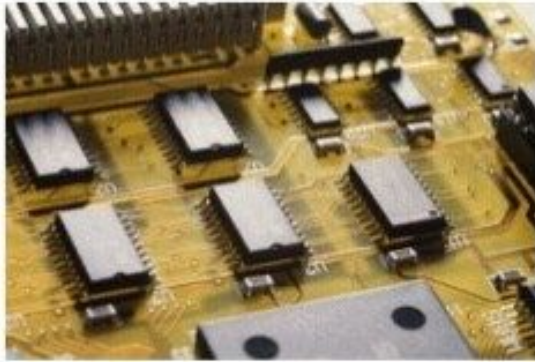
Introduction: Dilute Magnetic Semiconductors



Introduction: DMSs for Spintronics

Nearly incompatible technologies in present-day computers:

semiconductors: processing



ferromagnets: data storage

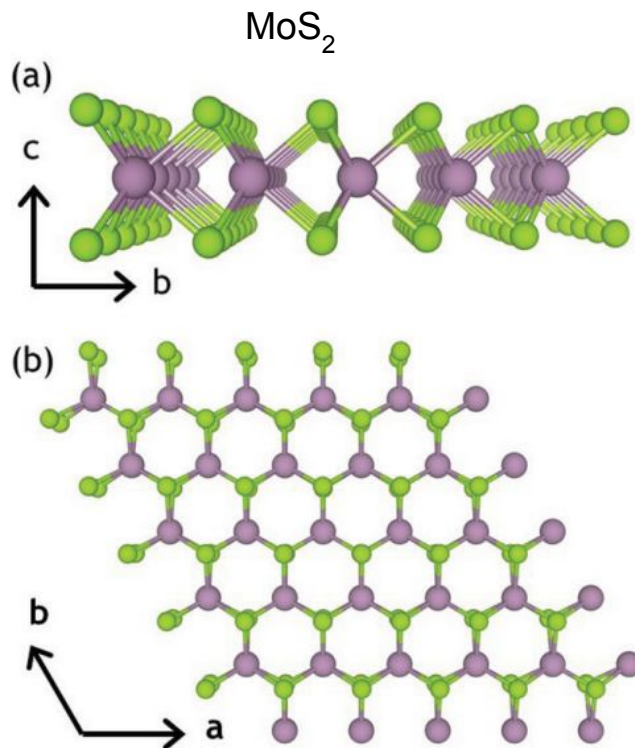


ferromagnetic semiconductors: integration on a single chip?

single-chip computers for embedded applications:
cell phones, intelligent appliances, security

Transition Metal Dichalcogenide DMSs

- Existing monolayer exfoliation technology (nanoelectronics)
- Direct band gap ~ 2 eV suitable for semiconductor technology (shrinking transistors)
- Idea: substitute Mo^{4+} with Mn^{4+} , extra 3d valence electron acts to break spin degeneracy, emergent magnetism.



Outline of Paper

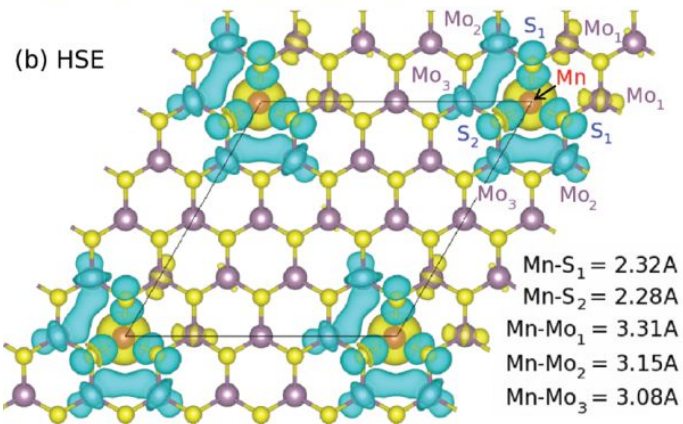
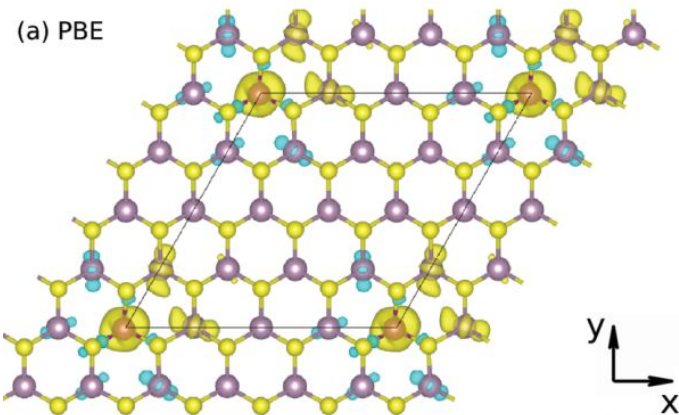
- Use Density Functional Theory (DFT) to calculate magnetic ground state properties and exchange coupling constants.
- Map DFT parameters to Heisenberg model, use statistical methods (Monte Carlo) to approximate thermal properties of the material.
- Conclusions: room temp. Ferromagnetism emerges from short-ranged double-exchange interactions in Mn/MoS_2 for dopant concentrations around 10-15%.

Predictions of DFT

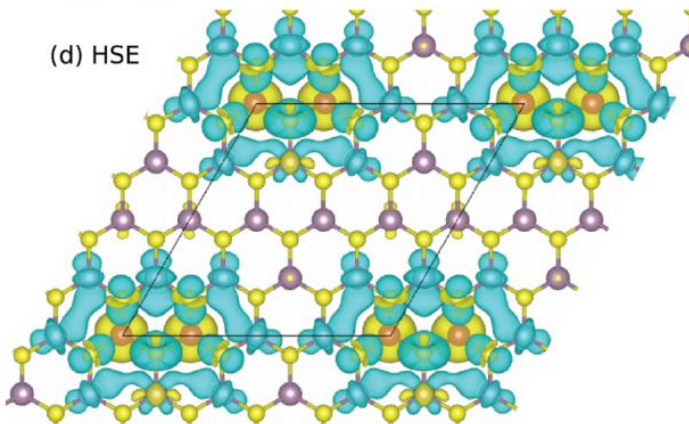
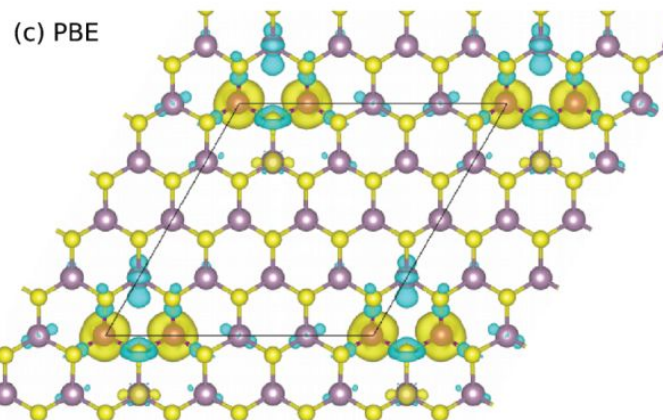
- Basic idea: calculate many-body ground state electronic density from effective single-electron theory, only depends on material crystal structure.
- Comparison of standard model (PBE) with hybrid DFT (HSE).
 - PBE has been shown to predict excessive delocalization of d orbital wavefunctions, leads to inaccurate interaction parameters.
 - HSE corrects for self-interaction errors in standard DFT, improvement of DFT predictions.
- HSE predictions for MoS_2 band gap agree more closely with experiment.

Predictions of DFT: Spin Density

6.25% Mn doping

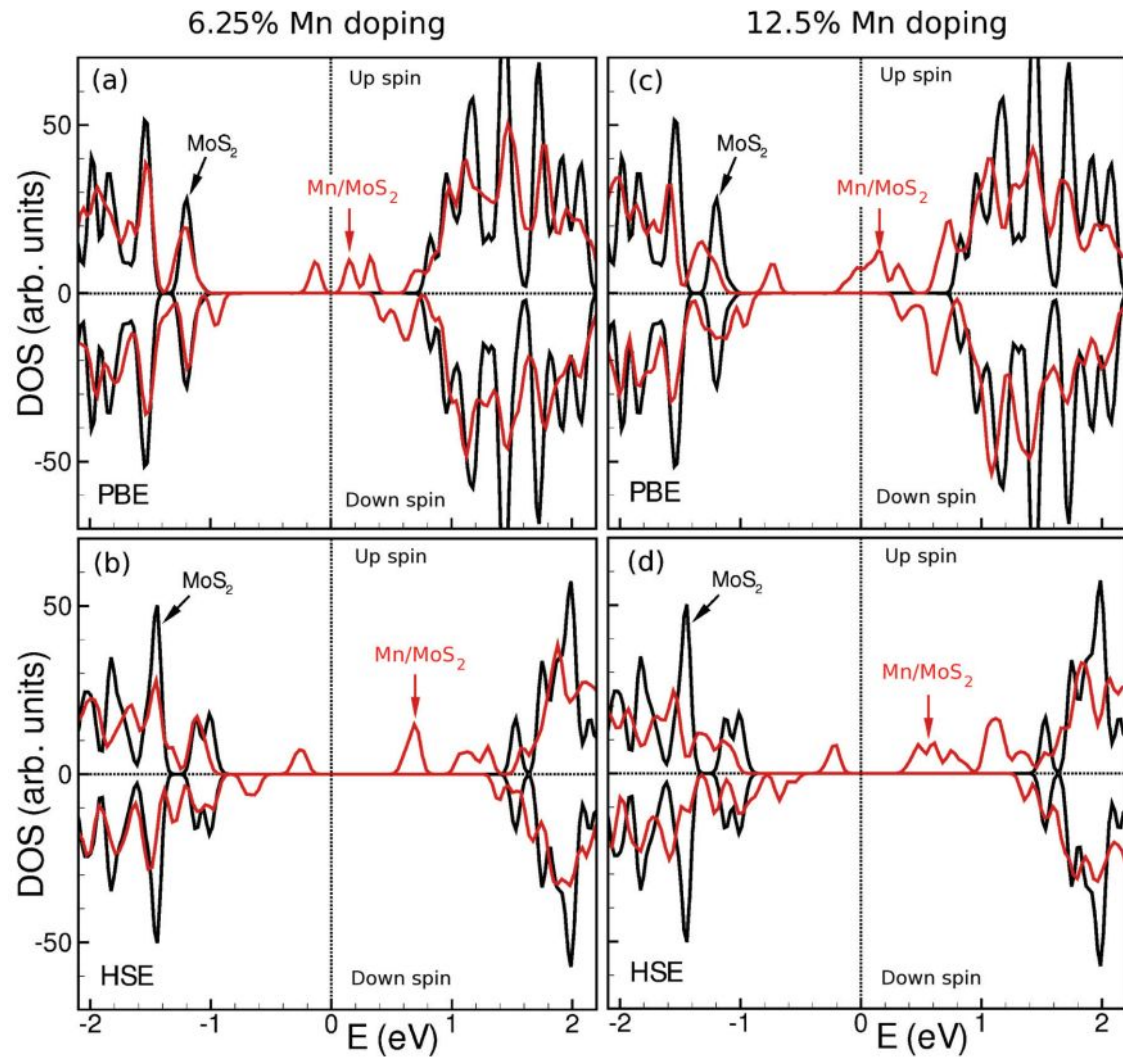


12.5% Mn doping

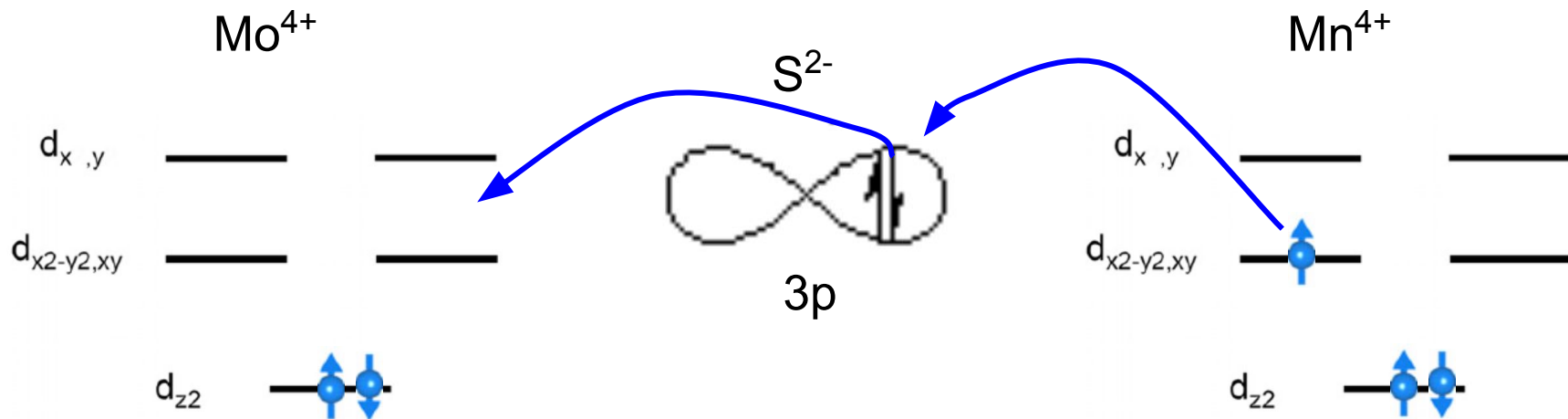


Predictions of DFT: Electronic Density of States

- Mn substitution breaks spin degeneracy, in-gap defect states emerge.
- The two DFT theories have relative shift in energies, leads to half-metallic behavior for PBE model.



Double-exchange Mechanism



Estimating Magnetic Interaction Parameters

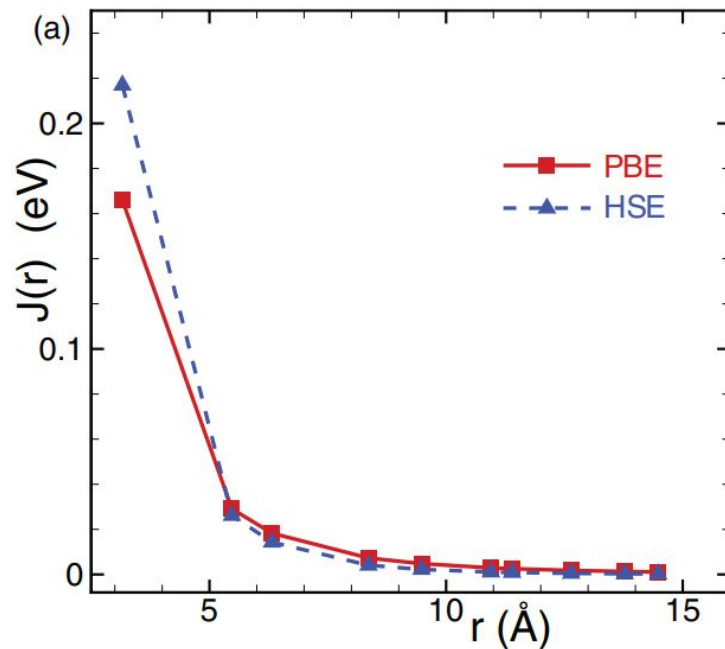
Parameterize interaction with DFT predictions

Supercell	Configuration	Δ_{AFM-FM} (eV)		ΔE_{FM} (eV)	
		PBE	HSE	PBE	HSE
4×4	1 st n.n.	0.18	0.22	0.0	0.0
	2 nd n.n.	0.06	0.07	0.37	0.66
	3 rd n.n.	0.03	-0.00	0.43	0.65
6×6	1 st n.n.	0.17			
8×8	1 st n.n.	0.17			

Heisenberg Model

$$H = -J \sum_{i,j} \vec{S}_i \cdot \vec{S}_j$$

$$J(r) = \begin{cases} \frac{c}{r^3} \exp[-r/r_0], & \text{if } r \leq r_c \\ 0, & \text{otherwise} \end{cases},$$



Monte Carlo Simulation

- Mean-field theory inaccurately predicts magnetic ordering temperature, need to account for spatial disorder.
- Randomized simulation of Mn spins on triangular lattice, estimate percolation threshold.
- Critical temperature for ferromagnetism for Mn concentrations $\sim 15\%$.

